

This activity is synergetic to the EIC-SVT work and it is independently funded by STFC Nat Labs internal funds.

Dosimetry in SiO₂: update on Geant4

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Introduction

- X-ray generators are useful tools to test TID effects on ICs.

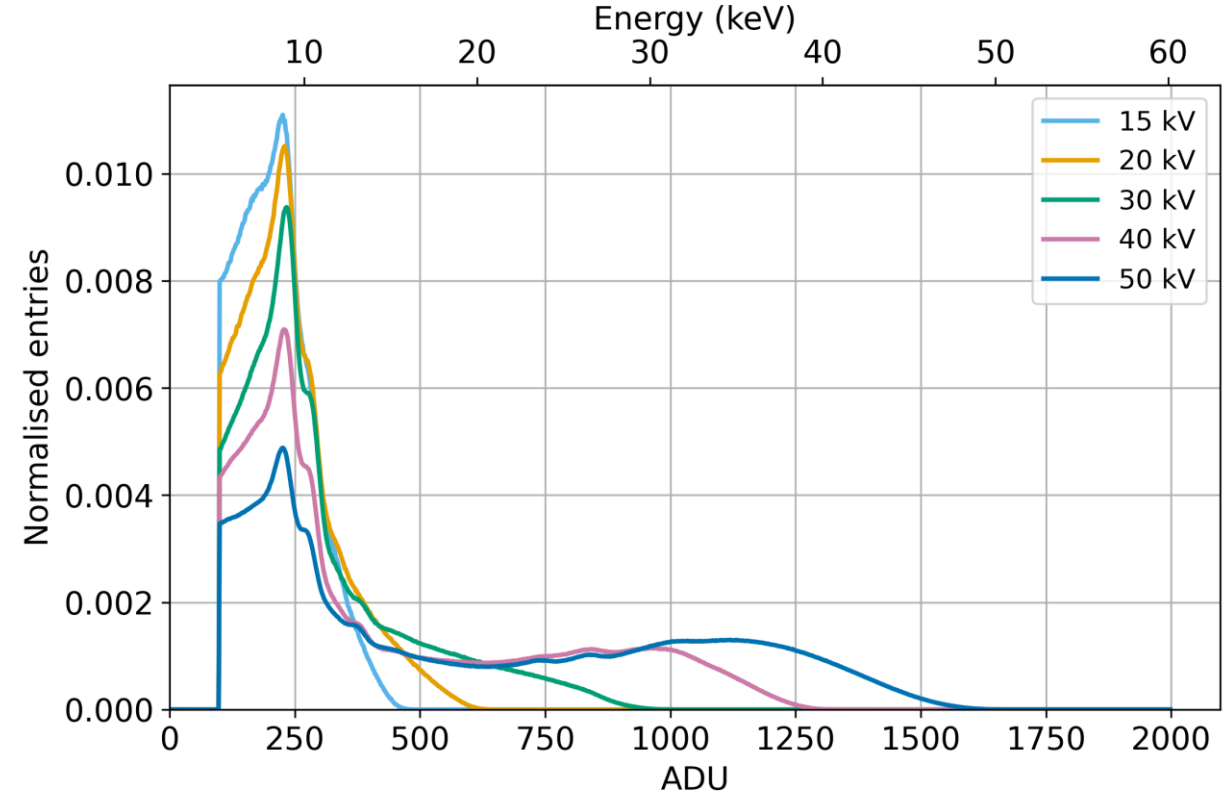
- Quicker than Co60...
- ... particularly useful at high integrated dose.
- See the exploratory irradiations up to ~3 Grad of the ER1 RAL IC. (~28 days, 24/7 at ~100krad/min).

- Calibration of X-ray generator at DL is based on calibration procedure from CERN:

- This lacks transparency and requires a leap of faith;
- **Liam** submitted an **internal proposal** to improve our understanding of dosimetry (~5k GBP i.e. only consumables). Proposal in **collaboration with RAL** (F.Wilson, C.Sawyer).

- Three things in this project:

- **Simulate the physics of energy deposition in matter;**
- Perform half value layer measurements with an ionisation chamber;
- Perform dose measurements with radio chromic foils;

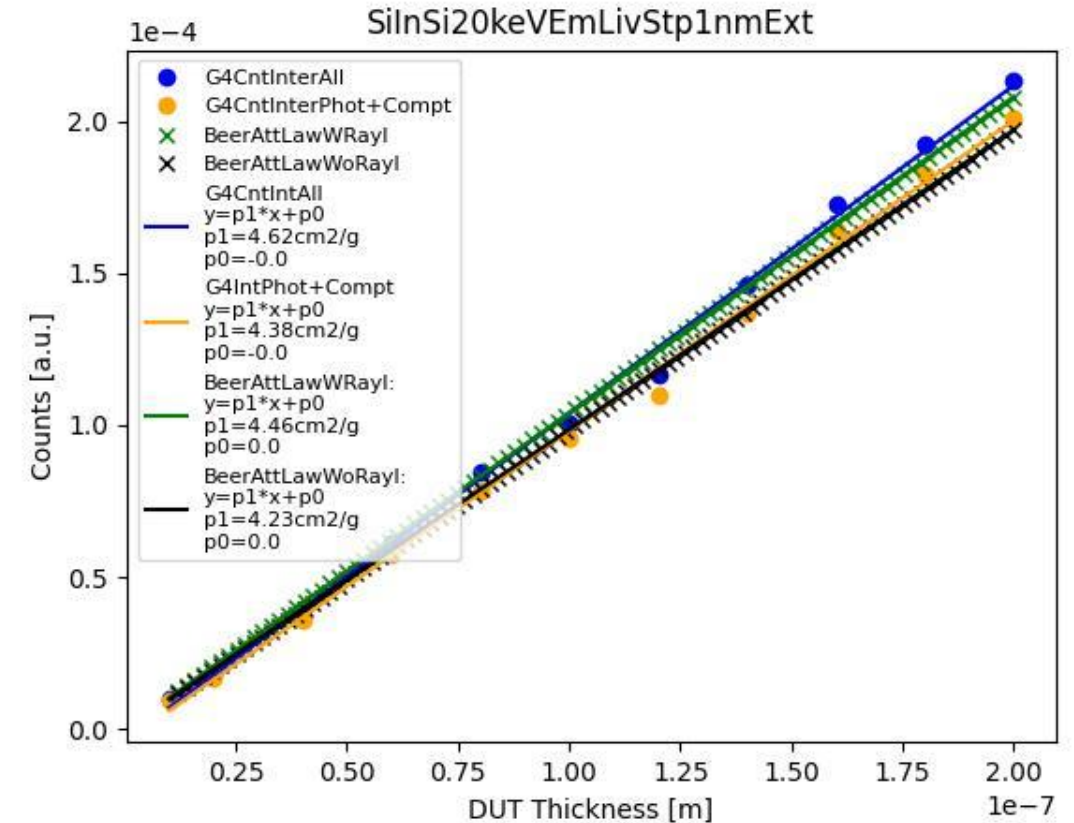


CERN target dose rate : 100krad/min (recommended)

DL measured dose rate : 104krad/min at **20kV** 20mA

Update about Geant4 simulations - attenuation

- Selected Geant4 as simulation framework
- Geometry: thin sheet (10's -100's nm)
- Beam: monochromatic X-rays
 - Sampled 4 energies: [5keV, 10keV, 15keV, 20keV]
- Physics list:
 - Livermore Electromagnetic (only);
- Successfully replicated the reciprocal to 1 of the Beer-Lambert law in thin sheet ($d \sim 0$).
 - $f(x) = 1 - (I/I_0) = 1 - e^{(-d \cdot \mu)}$
 - μ = mass attenuation coefficient;



Update about Geant4 simulations – Mass Energy Absorption

- Validated a key formula for dose evaluation:

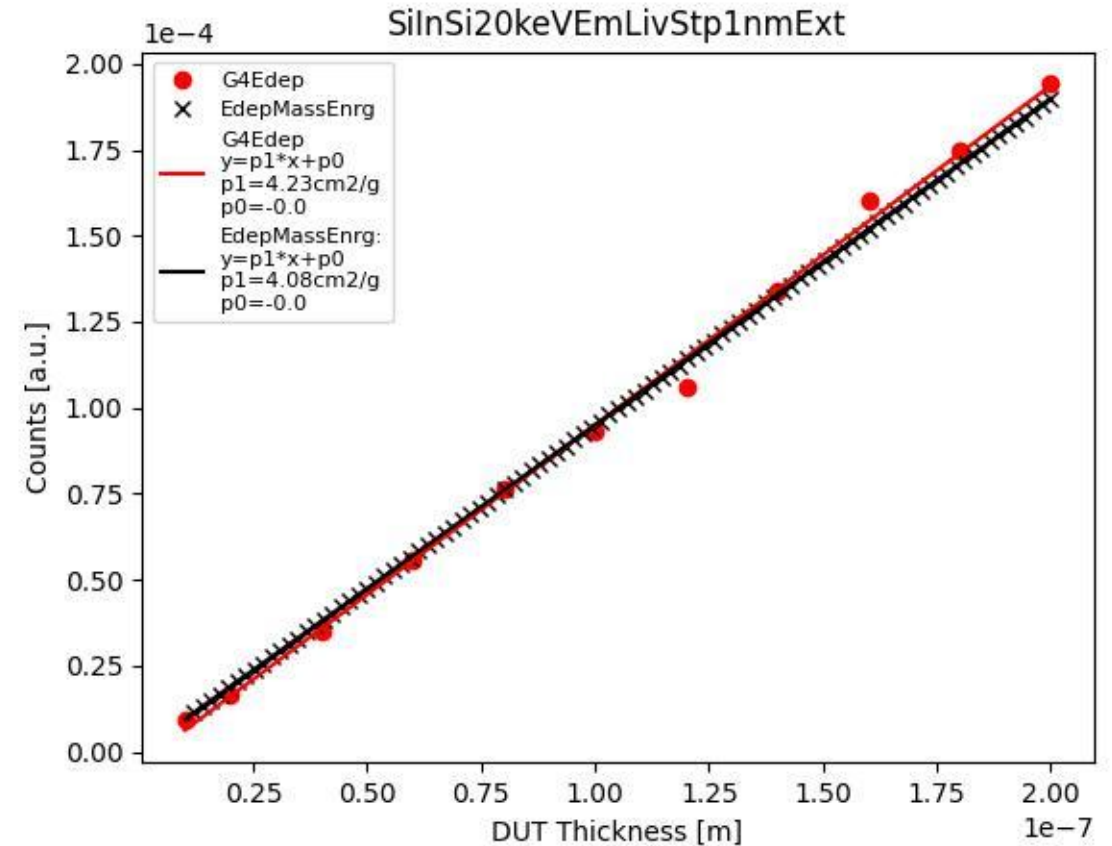
- $D = \phi * E * \mu_{en}$

- D = dose [Energy/Mass];
- ϕ = flux/area [# / area]; (Dependent on Bee-Lamber law)
- E = energy [Energy];
- μ_{en} = mass-energy absorption coeff. [Area/Mass];

- Valid for thickness ~ 0 and in charge particle equilibrium etc...

- i.e. **Edep increases linearly with thickness, when thickness ~ 0 .**

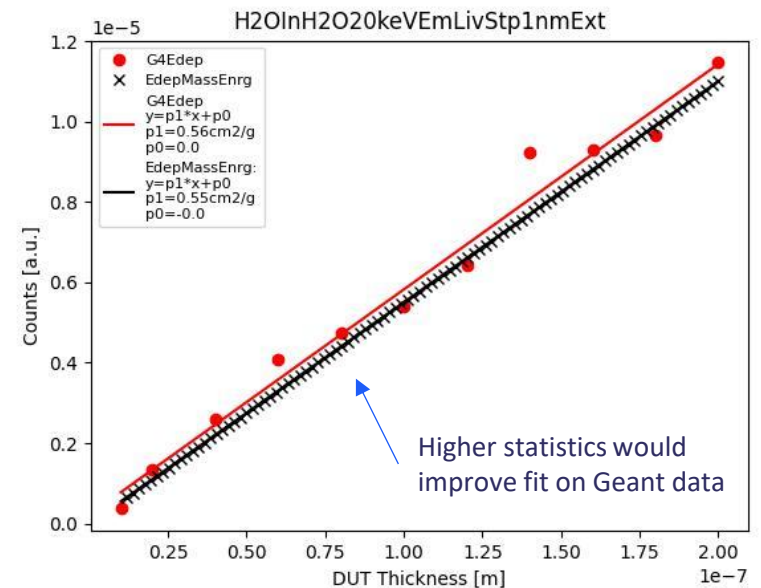
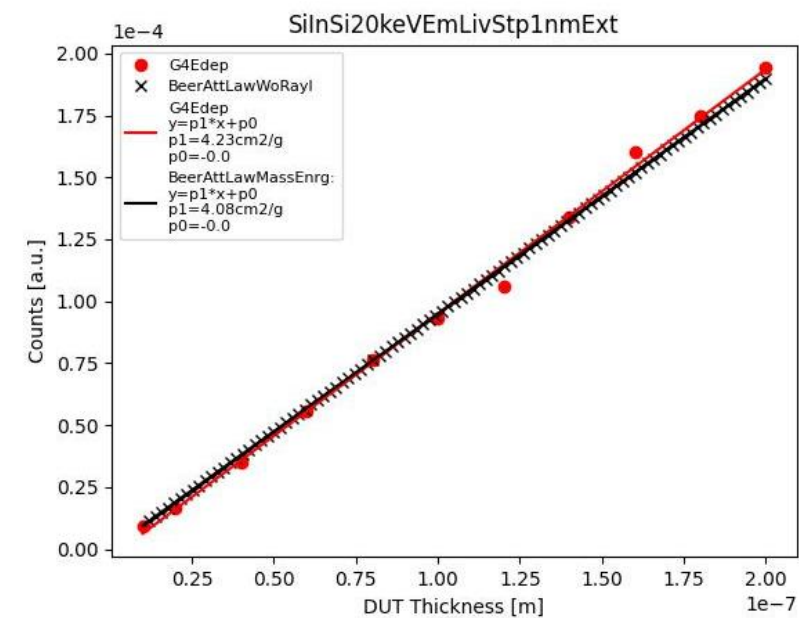
- i.e. dose is independent of thickness when thickness ~ 0 .



Update about Geant4 simulations – Energy conversion

- Energy conversion validation between Si and H2O.
- Si: $D1 = \phi_1 \cdot E1 \cdot \mu_{en1}$
- H2O: $D2 = \phi_2 \cdot E2 \cdot \mu_{en2}$
- Samples irradiated under the same conditions:
 - $\phi_1 = \phi_2$; $E1 = E2$;
- $D1/D2 = \mu_{en1}/\mu_{en2}$;
- $D1 = D2 \cdot (\mu_{en1}/\mu_{en2})$;
- Dose ratio comparison at 20keV: (μ_{en1}/μ_{en2})
- NIST db:
 - $4.076E+00 \text{ [cm}^2/\text{g}] / 5.503E-01 \text{ [cm}^2/\text{g}] = 7.4$;
- G4:
 - $4.23E+00 \text{ [cm}^2/\text{g}] / 5.6E-01 \text{ [cm}^2/\text{g}] = 7.55$;

~2% discrepancy
from NIST



Conclusion

- We successfully validated Geant4 against theory/experimental data.
- Setting up Geant4 and running qualitative examples was (fairly) straight forward; (well documented)
- It was hard to achieve quantitatively reliable results for our specific application [5 months Liam and Marcello]:
 - Lack of directly applicable literature
 - Micro dosimetry in medical applications focusses on H₂O;
 - Micro dosimetry in micro-electronics focusses on e⁻, p⁺, and ions;
 - Bugs in G4 NIST database; [SiO₂ material has wrong density]
 - Selecting correct physics list and processes;
 - Setting correct max step parameters;
 - Setting correct particle production threshold;
 - Not to use function “GetTotalEnergyDeposit()” in “Step”;
- Next: to model the real beam shape in Geant4 (inc. HVL measurements), and to practice conversion H₂O to SiO₂